



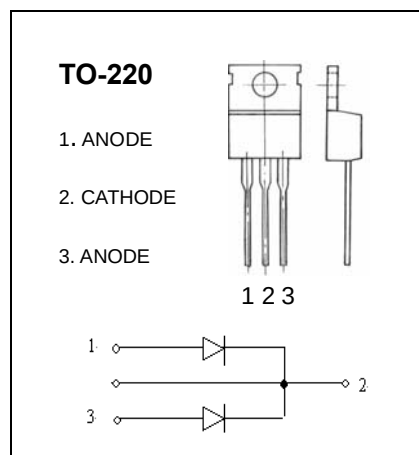
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

MBR20200CT SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Output Current (Note 1) @ T _c =125°C	I_O	20	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150	A
Repetitive Peak Reverse Surge Current @ t ≤ 2.0μs	I_{RRM}	1	A
Forward Voltage Drop @ I _F =10A, T _c =25°C @ I _F =10A, T _c =125°C @ I _F =20A, T _c =25°C @ I _F =20A, T _c =125°C	V_{FM}	0.95 0.8 1.0 0.9	V
Peak Reverse Current @ T _c = 25°C at Rated DC Blocking Voltage @ T _c =125°C	I_{RM}	1 50	mA
Typical Junction Capacitance (Note 2)	C_j	500	pF
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

Notes: 1. Thermal resistance junction to case mounted heat sink.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.